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74VCX164245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

General Description

The VCX164245 is a dual supply, 16-bit translating transceiver that is designed for two way asynchronous communication between busses at different supply voltages by providing true signal translation. The supply rails consist of V_{CCB}, which is the higher potential rail operating at 2.3V to 3.6V and V_{CCA}, which is the lower potential rail operating at 1.65V to 2.7V. (V_{CCA} must be less than or equal to V_{CCB} for proper device operation.) This dual supply design allows for translation from 1.8V to 2.5V busses to busses at a higher potential, up to 3.3V.

The Transmit/Receive (T/ \overline{R}) input determines the direction of data flow. Transmit (active-HIGH) enables data from A Ports to B Ports. Receive (active-LOW) enables data from B Ports to A Ports. The Output Enable (\overline{OE}) input, when HIGH, disables both A and B Ports by placing them in a High-Z condition. The A Port interfaces with the lower voltage bus (1.8V – 2.5V). The B Port interfaces with the higher voltage bus (2.7V – 3.3V). Also the VCX164245 is designed so that the control pins (T/ \overline{R}_n , \overline{OE}_n) are supplied by V_{CCB}.

The 74VCX164245 is suitable for mixed voltage applications such as notebook computers using a 1.8V CPU and 3.3V peripheral components. It is fabricated with an Advanced CMOS technology to achieve high speed operation while maintaining low CMOS power dissipation.

Features

- Bidirectional interface between busses ranging from 1.65V to 3.6V
- Supports Live Insertion and Withdrawal (Note 1)
- Static Drive (I_{OH}/I_{OL})
 - ±24 mA @ 3.0V V_{CC}
 - \pm 18 mA @ 2.3V V_{CC}
 - ±6 mA @ 1.65V V_{CC}
- Uses proprietary noise/EMI reduction circuitry
- Functionally compatible with 74 series 16245
- Latchup performance exceeds 300 mA
- ESD performance:
 - Human Body Model >2000V
 - Machine model >200V
- Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

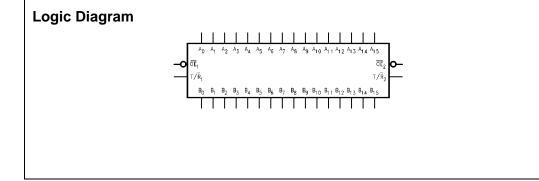
Note 1: To ensure the high impedance state during power up or power down, OE_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver.

Ordering Code:

Order Number	Package Number	Package Description
74VCX164245G (Note 2)(Note 3)	BGA54A	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74VCX164245MTD (Note 3)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Note 2: Ordering Code "G" indicates Trays.

Note 3: Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.



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74VCX164245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

74VCX164245

Pin Assignment for TSSOP T/\overline{R}_1 - OE 48 47 B₀ - A₀ 46 B₁ GND · 45 GND 44 A2 B₂ -43 B3 - A3 42 - V_{CCA} V_{ССВ} 4 1 84 — A4 40 A5 39 GND B₅ -GND • 10 38 – A₆ В₆ -12 37 A7 B₇ -36 - A₈ 13 В₈ -Bg 1.4 35 - Ag - GND GND · 15 34 B₁₀ · 16 33 A₁₀ 32 A₁₁ 31 V_{CCA} 17 B11 -V_{CCB} · 18 30 - A₁₂ 19 B₁₂ -29 A₁₃ 20 B₁₃ • 21 28 - GND GND . - A_{1.4} B₁₄ 22 27 26 A₁₅ B₁₅ 23 25 - OE2 T/\bar{R}_2 24 Pin Assignment for FBGA 1 2 3 4 5 6 000000 ∢ ш 000000 υ 000000 Δ 000000 ш 000000 ш 000000 G 000000 000000 т 000000

Connection Diagrams

(Top Through View)

Pin Descriptions

Pin Names	Description
OEn	Output Enable Input (Active LOW)
T/R _n	Transmit/Receive Input
A ₀ -A ₁₅ B ₀ -B ₁₅ NC	Side A Inputs or 3-STATE Outputs
B ₀ -B ₁₅	Side B Inputs or 3-STATE Outputs
NC	No Connect

FBGA Pin Assignments

	1	2	3	4	5	6
Α	B ₀	NC	T/R ₁	OE ₁	NC	A ₀
В	B ₂	B ₁	NC	NC	A ₁	A ₂
С	B ₄	B ₃	V _{CCB}	V _{CCA}	A ₃	A ₄
D	B ₆	B ₅	GND	GND	A ₅	A ₆
E	B ₈	В ₇	GND	GND	A ₇	A ₈
F	B ₁₀	B ₉	GND	GND	A ₉	A ₁₀
G	B ₁₂	B ₁₁	V _{CCB}	V _{CCA}	A ₁₁	A ₁₂
Н	B ₁₄	B ₁₃	NC	NC	A ₁₃	A ₁₄
J	B ₁₅	NC	T/R_2	OE ₂	NC	A ₁₅

Truth Tables

Inp	outs				
OE ₁	T/R ₁	Outputs			
L	L	Bus B ₀ –B ₇ Data to Bus A ₀ –A ₇			
L	н	Bus $A_0 - A_7$ Data to Bus $B_0 - B_7$			
н	х	HIGH Z State on A ₀ -A ₇ , B ₀ -B ₇			
Inp	outs				
Inp OE ₂	outs T/R ₂	Outputs			
· ·	_	Outputs Bus B ₈ -B ₁₅ Data to Bus A ₈ -A ₁₅			
· ·	_	•			

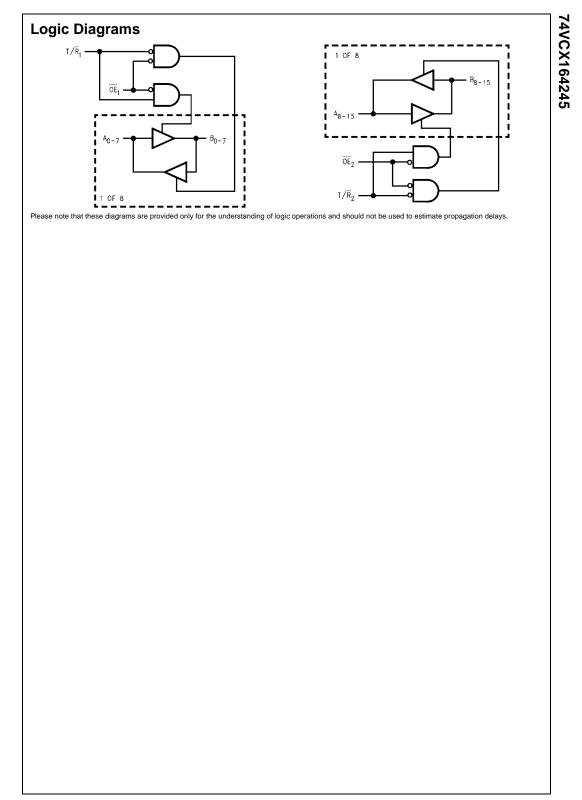
H = HIGH Voltage Level L = LOW Voltage Level

X = Immaterial (HIGH or LOW, inputs may not float)

Z = High Impedance

Translator Power Up Sequence Recommendations

To guard against power up problems, some simple guidelines need to be adhered to. The VCX164245 is designed so that the control pins (T/ \overline{R}_n , \overline{OE}_n) are supplied by V_{CCB}. Therefore the first recommendation is to begin by powering up the control side of the device, V_{CCB}. The \overline{OE}_n control pins should be ramped with or ahead of V_{CCB}, this will guard against bus contentions and oscillations as all A Port and B Port outputs will be disabled. To ensure the high impedance state during power up or power down, \overline{OE}_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver. Second, the T/\overline{R}_n control pins should be placed at logic low (0V) level, this will ensure that the B-side bus pins are configured as inputs to help guard against bus contention and oscillations. B-side Data Inputs should be driven to a valid logic level (0V or V_{CCB}), this will prevent excessive current draw and oscillations. V_{CCB} , this will prevent excessive current draw and oscillations. V_{CCB} can then be powered up after V_{CCB} , but should never exceed the V_{CCB} voltage level. Upon completion of these steps the device can then be configured for the users desired operation. Following these steps will help to prevent possible damage to the translator device as well as other system components.



Absolute Maximum Ratings(Note 4)

Recommended Operating Conditions (Note 6)

Supply Voltage		Conditions (Note 6)	
V _{CCA}	–0.5V to V _{CCB}	Power Supply (Note 7)	
V _{CCB}	-0.5V to 4.6V	V _{CCA}	1.65V to 2.7V
DC Input Voltage (VI)	-0.5V to +4.6V	V _{CCB}	2.3V to 3.6V
DC Output Voltage (V _{I/O})		Input Voltage (V _I) @ OE, T/R	0V to V _{CCB}
Outputs 3-STATE	-0.5V to +4.6V	Input/Output Voltage (VI/O)	
Outputs Active (Note 5)		A _n	0V to V _{CCA}
An	–0.5V to V_{CCA} + 0.5V	B _n	0V to V _{CCB}
Bn	–0.5V to V_{CCB} + 0.5V	Output Current in I _{OH} /I _{OL}	
DC Input Diode Current (I _{IK})		$V_{CCA} = 2.3V$ to 2.7V	±18 mA
$V_{I} < 0V$	–50 mA	V _{CCA} = 1.65V to 1.95V	±6 mA
DC Output Diode Current (I _{OK})		V _{CCB} = 3.0V to 3.6V	±24 mA
$V_{O} < 0V$	–50 mA	$V_{CCB} = 2.3V$ to 2.7V	±18 mA
$V_{O} > V_{CC}$	+50 mA	Free Air Operating Temperature (T _A)	-40°C to +85°C
DC Output Source/Sink Current	±50 mA	Minimum Input Edge Rate ($\Delta t / \Delta V$)	
(I _{OH} /I _{OL})		$V_{IN} = 0.8V$ to 2.0V, $V_{CC} = 3.0V$	10 ns/V
DC V _{CC} or Ground Current	±100 mA	Note 4: The "Absolute Maximum Ratings" are thos	
Supply Pin (I _{CC} or Ground)		the safety of the device cannot be guaranteed. The operated at these limits. The parametric values d	
Storage Temperature (T _{STG})	-65°C to +150°C	Characteristics tables are not guaranteed at the abs The "Recommended Operating Conditions" table w for actual device operation.	

Note 5: I_O Absolute Maximum Rating must be observed.

Note 6: Unused inputs or I/O pins must be held HIGH or LOW. They may not float.

Note 7: Operation requires: $V_{CCA} \leq V_{CCB}$

DC Electrical Characteristics (1.65V $< V_{CCA} \leq$ 1.95V, 2.3V $< V_{CCB} \leq$ 2.7V)

Symbol	Parameter		Conditions	V _{CCA} (V)	V _{ССВ} (V)	Min	Max	Units
V _{IHA}	HIGH Level Input Voltage	A _n		1.65-1.95	2.3–2.7	0.65 x V _{CC}		V
V _{IHB}		B _n , T/R, OE		1.65-1.95	2.3-2.7	1.6		V
V _{ILA}	LOW Level Input Voltage	A _n		1.6-1.95	2.3-2.7		$0.35 \times V_{CC}$	V
VILB		B _n , T/R, OE		1.65-1.95	2.3-2.7		0.7	V
V _{OHA}	HIGH Level Output Voltage	e	I _{OH} = -100 μA	1.65-1.95	2.3-2.7	V _{CCA} -0.2		V
			I _{OH} = -6 mA	1.65	2.3-2.7	1.25		v
V _{OHB}	HIGH Level Output Voltage	е	I _{OH} = -100 μA	1.65-1.95	2.3-2.7	V _{CCB} -0.2		V
			I _{OH} = -18 mA	1.65-1.95	2.3	1.7		v
V _{OLA}	LOW Level Output Voltage)	I _{OL} = 100 μA	1.65-1.95	2.3–2.7		0.2	V
			$I_{OL} = 6 \text{ mA}$	1.65	2.3–2.7		0.3	•
V _{OLB}	LOW Level Output Voltage		I _{OL} = 100 μA	1.65-1.95	2.3–2.7		0.2	V
			I _{OL} = 18 mA	1.65-1.95	2.3		0.6	v
l _l	Input Leakage Current @	OE, T/R	$0V \leq V_{I} \leq 3.6V$	1.65-1.95	2.3–2.7		±5.0	μA
loz	3-STATE Output Leakage		$\frac{0V \le V_O \le 3.6V}{OE} = V_{CCB}$ $V_I = V_{IH} \text{ or } V_{IL}$	1.65–1.95	2.3–2.7		±10	μΑ
OFF	Power OFF Leakage Curre	ent	$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μA
I _{CCA} /I _{CCB}	Quiescent Supply Current, per supply, V _{CCA} / V _{CCB}		$A_n = V_{CCA}$ or GND B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND	1.65–1.95	2.3–2.7		20	μA
			$\label{eq:V_CCA} \begin{split} & V_{CCA} \leq A_n \leq 3.6V \\ & V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{split}$	1.65–1.95	2.3–2.7		±20	μA
۵I _{CC}	Increase in I _{CC} per Input, I	B _n , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65-1.95	2.3–2.7		750	μA
	Increase in I _{CC} per Input, /	۹ _n	$V_I = V_{CCA} - 0.6V$	1.65-1.95	2.3-2.7	1	750	μA

Symbol	Pa	rameter	Conditions	V _{CCA} (V)	V _{ССВ} (V)	Min	Max	Units	
V _{IHA}	HIGH Level	A _n		1.65–1.95	3.0–3.6	0.65 x V _{CC}		V	
V _{IHB}	Input Voltage	B _n , T/R, OE		1.65-1.95	3.0–3.6	2.0		V	
V _{ILA}	LOW Level	A _n		1.65-1.95	3.0-3.6		0.35 x V _{CC}	V	
V _{ILB}	Input Voltage	B _n , T/R, OE		1.65-1.95	3.0-3.6		0.8	V	
V _{OHA}	HIGH Level Outp	ut Voltage	I _{OH} = -100 μA	1.65-1.95	3.0-3.6	V _{CCA} -0.2			
			I _{OH} = -6 mA	1.65	3.0-3.6	1.25		V	
V _{OHB}	HIGH Level Outp	out Voltage	I _{OH} = -100 μA	1.65-1.95	3.0-3.6	V _{CCA} -0.2		v	
			I _{OH} = -24 mA	1.65-1.95	3.0	2.2			
V _{OLA}	LOW Level Outpo	ut Voltage	I _{OL} = 100 μA	1.65–1.95	3.0-3.6		0.2	V	
			$I_{OL} = 6 \text{ mA}$	1.65	3.0-3.6		0.3	v	
V _{OLB}	LOW Level Outpo	ut Voltage	I _{OL} = 100 μA	1.65–1.95	3.0–3.6		0.2	V	
			$I_{OL} = 24 \text{ mA}$	1.65–1.95	3.0		0.55	v	
l _l	Input Leakage Cu	urrent @ OE, T/R	$0V \leq V_I \leq 3.6V$	1.65-1.95	3.0-3.6		±5.0	μA	
l _{oz}	3-STATE Output	Leakage	$0V \leq V_O \leq 3.6V$						
			$OE^{\star} = V_{CCB}$	1.65–1.95	3.0-3.6		±10	μA	
			$V_I = V_{IH} \text{ or } V_{IL}$						
I _{OFF}	Power Off Leaka	ge Current	$0 \leq (V_I, V_O) \leq 3.6V$	0	0		10	μA	
I _{CCA} /I _{CCB}	Quiescent Supply	y Current,	$A_n = V_{CCA}$ or GND	1.65-1.95	3.0-3.6		20	μA	
	per supply, V _{CCA}	N _{CCB}	B_n , \overline{OE} , & $T/R = V_{CCB}$ or GND	1.00 1.00	0.0 0.0		20	μ	
			$V_{CCA} \leq A_n \leq 3.6V$	1.65-1.95	3.0-3.6		±20	шA	
			$V_{CCB} \le B_n$, \overline{OE} , $T/R \le 3.6V$		0.0			Ļ.	
∆l _{CC}	Increase in I _{CC} p	er Input, B _n , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65–1.95	3.0–3.6		750	μA	
	Increase in I _{CC} p	er Input, A _n	$V_I = V_{CCA} - 0.6V$	1.65-1.95	3.0-3.6	1	750	uА	

DC Electrical Characteristics (2.3V < V_{CCA} \leq 2.7V, 3.0V \leq V_{CCB} \leq 3.6V)

Symbol	Parameter		Conditions	V _{CCA} (V)	V _{ССВ} (V)	Min	Max	Units
V _{IHA}	HIGH Level Input Voltage	A _n		2.3–2.7	3.0-3.6	1.6		V
V _{IHB}		B _n , T/R, OE		2.3–2.7	3.0-3.6	2.0		V
V _{ILA}	LOW Level Input Voltage	A _n		2.3–2.7	3.0-3.6		0.7	V
V _{ILB}		B _n , T/R, OE		2.3–2.7	3.0-3.6		0.8	V
V _{OHA}	HIGH Level Output Voltage	e	I _{OH} = -100 μA	2.3–2.7	3.0-3.6	V _{CCA} -0.2		v
			I _{OH} = -18 mA	2.3	3.0-3.6	1.7		v
V _{ОНВ}	HIGH Level Output Voltage	е	I _{OH} = -100 μA	2.3–2.7	3.0-3.6	V _{CCB} -0.2		v
			$I_{OH} = -24 \text{ mA}$	2.3–2.7	3.0	2.2		
V _{OLA}	LOW Level Output Voltage	9	I _{OL} = 100 μA	2.3–2.7	3.0-3.6		0.2	v
			I _{OL} = 18 mA	2.3	3.0-3.6		0.6	
V _{OLB}	LOW Level Output Voltage)	I _{OL} = 100 μA	2.3–2.7	3.0-3.6		0.2	v
			$I_{OL} = 24 \text{ mA}$	2.3–2.7	3.0		0.55	v
l _l	Input Leakage Current @	OE, T/R	$0V \leq V_I \leq 3.6V$	2.3–2.7	3.0-3.6		±5.0	μA
l _{oz}	3-STATE Output Leakage	@ A _n	$\frac{0V \le V_O \le 3.6V}{OE} = V_{CCA}$ $V_I = V_{IH} \text{ or } V_{IL}$	2.3–2.7	3.0–3.6		±10	μA
I _{OFF}	Power OFF Leakage Curre	ent	$0 \leq \left(V_{I}, V_{O}\right) \leq 3.6 V$	0	0		10	μΑ
I _{CCA} /I _{CCB}	Quiescent Supply Current, per supply, V _{CCA} /V _{CCB}		$A_n = V_{CCA}$ or GND B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND	2.3–2.7	3.0–3.6		20	μA
			$ \begin{array}{l} V_{CCA} \leq A_n \leq 3.6V \\ V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{array} $	2.3–2.7	3.0–3.6		±20	μΑ
∆l _{CC}	Increase in I _{CC} per Input, I	B _n , T/R, OE	$V_I = V_{CCB} - 0.6V$	2.3–2.7	3.0-3.6		750	μA
	Increase in I _{CC} per Input, /	۹ _n	$V_I = V_{CCA} - 0.6V$	2.3-2.7	3.0-3.6		750	μA

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AC Electrical Characteristics

Symbol			$C_L = 30 \text{ pF}, R_L = 500\Omega, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C},$						
	Parameter		V _{CCA} = 1.65V to 1.95V V _{CCB} = 2.3V to 2.7V		$V_{CCA} = 1.65V \text{ to } 1.95V$ $V_{CCB} = 3.0V \text{ to } 3.6V$		$V_{CCA} = 2.3V \text{ to } 2.7V$ $V_{CCB} = 3.0V \text{ to } 3.6V$		
		Min	Max	Min	Max	Min	Max		
t _{PHL} , t _{PLH}	Propagation Delay, A to B	0.8	5.5	0.6	5.1	0.6	4.0	ns	
t _{PHL} , t _{PLH}	Propagation Delay, B to A	1.5	5.8	1.5	6.2	0.8	4.4	ns	
t _{PZL} , t _{PZH}	Output Enable Time, OE to B	0.8	5.3	0.6	5.1	0.6	4.0	ns	
t _{PZL} , t _{PZH}	Output Enable Time, OE to A	1.5	8.3	1.5	8.2	0.8	4.6	ns	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to B	0.8	5.2	0.8	5.6	0.8	4.8	ns	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to A	0.8	4.6	0.8	4.5	0.8	4.4	ns	
osHL	Output to Output Skew (Note 8)		0.5		0.5		0.75	ns	

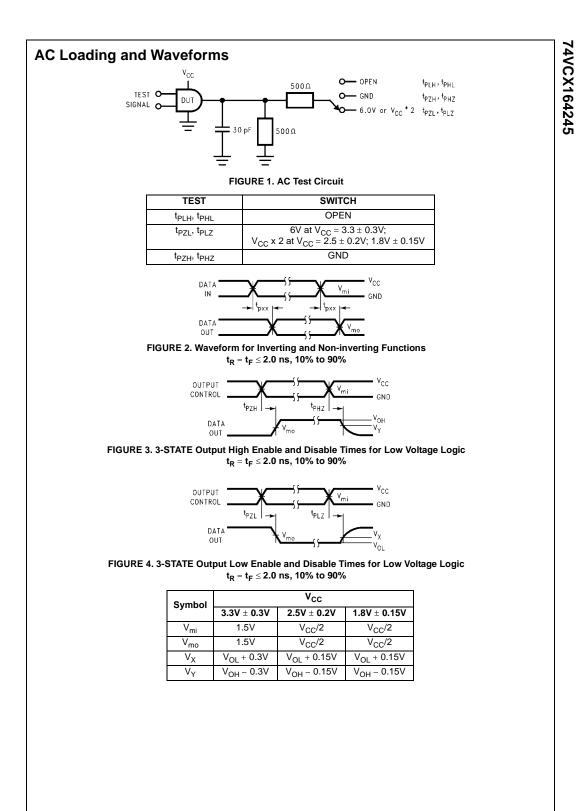
Note 8: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{osHL}) or LOW-to-HIGH (t_{osLH}).

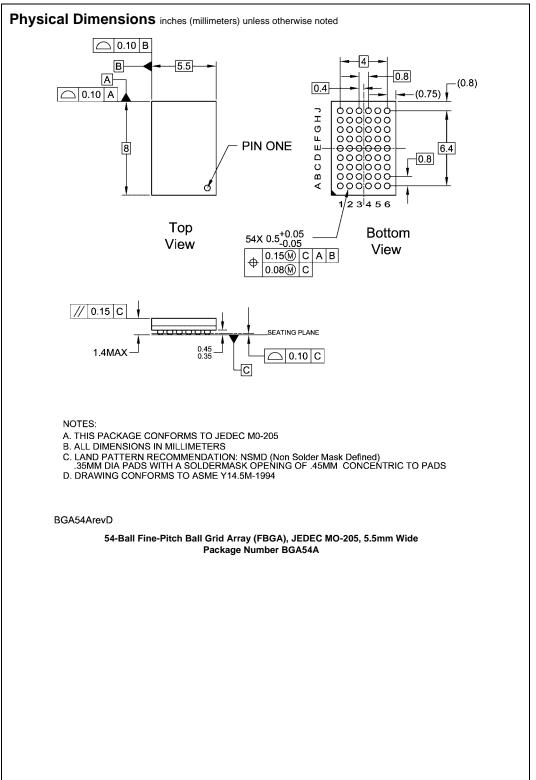
Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V _{CCA}	V _{CCB}	$T_A = 25^{\circ}C$	Units
	i di dificter	Conditions	(V)	(V)	Typical	Units
V _{OLP}	Quiet Output Dynamic Peak V _{OL} ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.25	
	B to A		1.8	3.3	0.25	V
			2.5	3.3	0.6	
	Quiet Output Dynamic Peak V _{OL} ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.6	
	A to B		1.8	3.3	0.8	V
			2.5	3.3	0.8	
V _{OLV}	Quiet Output Dynamic Valley V _{OL} ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.25	
	B to A		1.8	3.3	-0.25	V
			2.5	3.3	-0.6	
	Quiet Output Dynamic Valley V _{OL} ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.6	
	A to B		1.8	3.3	-0.8	V
			2.5	3.3	-0.8	
V _{OHV}	Quiet Output Dynamic Valley V _{OH} ,	$C_{L} = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	1.7	
	A to B		1.8	3.3	2.0	V
			2.5	3.3	2.0	
	Quiet Output Dynamic Valley V _{OH} ,	$C_L = 30 \text{ pF}, \text{ V}_{IH} = \text{V}_{CC}, \text{ V}_{IL} = 0 \text{V}$	1.8	2.5	1.3	
	B to A		1.8	3.3	1.3	V
			2.5	3.3	1.7	

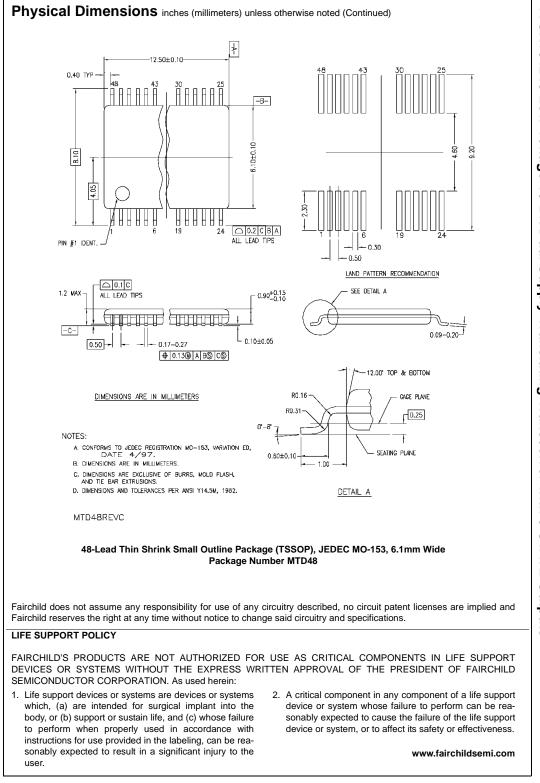
Capacitance

Symbol	Parameter	Conditions	T _A = +25°C Typical	Units
CIN	Input Capacitance	V_{CCA} = 2.5V, V_{CCB} = 3.3V, V_{I} = 0V or $V_{CCA/B}$	5	pF
C _{I/O}	Input/Output Capacitance	V_{CCA} = 2.5V, V_{CCB} = 3.3V, V_{I} = 0V or $V_{CCA/B}$	6	pF
C _{PD}		$\label{eq:VCCA} \begin{split} V_{CCA} &= 2.5 \text{V}, \ V_{CCB} = 3.3 \text{V}, \ \text{V}_{I} = 0 \text{V} \text{ or } \text{V}_{CCA/B} \\ \text{f} &= 10 \ \text{MHz} \end{split}$	20	pF





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⁷⁴VCX164245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

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